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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e300
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	400MHz
Co-Processors/DSP	Communications; QUICC Engine, Security; SEC
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (1)
SATA	-
USB	USB 1.x (1)
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	Cryptography, Random Number Generator
Package / Case	668-BBGA Exposed Pad
Supplier Device Package	668-PBGA-PGE (29x29)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/kmpc8358evragdda

- Advanced encryption standard unit (AESU)
- Implements the Rinjdael symmetric key cipher
- Key lengths of 128, 192, and 256 bits, two key
  - ECB, CBC, CCM, and counter modes
- ARC four execution unit (AFEU)
  - Implements a stream cipher compatible with the RC4 algorithm
  - 40- to 128-bit programmable key
- Message digest execution unit (MDEU)
  - SHA with 160-, 224-, or 256-bit message digest
  - MD5 with 128-bit message digest
  - HMAC with either SHA or MD5 algorithm
- Random number generator (RNG)
- Four crypto-channels, each supporting multi-command descriptor chains
  - Static and/or dynamic assignment of crypto-execution units via an integrated controller
  - Buffer size of 256 bytes for each execution unit, with flow control for large data sizes
- Storage/NAS XOR parity generation accelerator for RAID applications

- DDR SDRAM memory controller on the MPC8358E
  - Programmable timing supporting both DDR1 and DDR2 SDRAM
  - On the MPC8358E, the DDR bus can be configured as a 32- or 64-bit bus
  - 32- or 64-bit data interface, up to 266 MHz (for the MPC8358E) data rate
  - Four banks of memory, each up to 1 Gbyte
  - DRAM chip configurations from 64 Mbits to 1 Gigabit with ×8/×16 data ports
  - Full ECC support
  - Page mode support (up to 16 simultaneous open pages for DDR1, up to 32 simultaneous open pages for DDR2)
  - Contiguous or discontiguous memory mapping
  - Read-modify-write support
  - Sleep mode support for self refresh SDRAM
  - Supports auto refreshing
  - Supports source clock mode
  - On-the-fly power management using CKE
  - Registered DIMM support
  - 2.5-V SSTL2 compatible I/O for DDR1, 1.8-V SSTL2 compatible I/O for DDR2
  - External driver impedance calibration
  - On-die termination (ODT)
- PCI interface
  - PCI Specification Revision 2.3 compatible

4.3 Gigabit Reference Clock Input Timing

Table 8 provides the Gigabit reference clocks (GTX_CLK125) AC timing specifications.

Table 8. GTX_CLK125 AC Timing Specifications

At recommended operating conditions with LV_{DD} = 2.5 ± 0.125 mV/ 3.3 V ± 165 mV

Parameter/Condition	Symbol	Min	Typical	Max	Unit	Notes
GTX_CLK125 frequency	t_{G125}	—	125	—	MHz	—
GTX_CLK125 cycle time	t_{G125}	—	8	—	ns	—
GTX_CLK rise and fall time LV_{DD} = 2.5 V LV_{DD} = 3.3 V	t_{G125R}/t_{G125F}	—	—	 0.75 1.0	ns	1
GTX_CLK125 duty cycle GMII & TBI 1000Base-T for RGMII & RTBI	t_{G125H}/t_{G125}	 45 47	—	 55 53	%	2
GTX_CLK125 jitter	—	—	—	±150	ps	2

Notes:

1. Rise and fall times for GTX_CLK125 are measured from 0.5 and 2.0 V for LV_{DD} = 2.5 V and from 0.6 and 2.7 V for LV_{DD} = 3.3 V.
2. GTX_CLK125 is used to generate the GTX clock for the UCC Ethernet transmitter with 2% degradation. The GTX_CLK125 duty cycle can be loosened from 47%/53% as long as the PHY device can tolerate the duty cycle generated by GTX_CLK. See Section 8.2.2, “MII AC Timing Specifications,” Section 8.2.3, “RMII AC Timing Specifications,” and Section 8.2.5, “RGMII and RTBI AC Timing Specifications” for the duty cycle for 10Base-T and 100Base-T reference clock.

5 RESET Initialization

This section describes the DC and AC electrical specifications for the reset initialization timing and electrical requirements of the MPC8358E.

5.1 RESET DC Electrical Characteristics

Table 9 provides the DC electrical characteristics for the RESET pins of the device.

Table 9. RESET Pins DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit
Input high voltage	V_{IH}	—	2.0	OV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	–0.3	0.8	V
Input current	I_{IN}	—	—	±10	μA
Output high voltage	V_{OH}	I_{OH} = –8.0 mA	2.4	—	V
Output low voltage	V_{OL}	I_{OL} = 8.0 mA	—	0.5	V

Table 20. DDR and DDR2 SDRAM Output AC Timing Specifications for Source Synchronous Mode (continued)

At recommended operating conditions with GV_{DD} of (1.8 V or 2.5 V) ± 5%.

Parameter[8]	Symbol[1]	Min	Max	Unit	Notes
ADDR/CMD output setup with respect to MCK 266 MHz 200 MHz	t_{DDKHAS}	 2.8 3.5	—	ns	4
ADDR/CMD output hold with respect to MCK 266 MHz—DDR1 266 MHz—DDR2 200 MHz	t_{DDKHAX}	 2.6 2.8 3.5	—	ns	4
$\overline{MCS}$(n) output setup with respect to MCK 266 MHz 200 MHz	t_{DDKHCS}	 2.8 3.5	—	ns	4
$\overline{MCS}$(n) output hold with respect to MCK 266 MHz 200 MHz	t_{DDKHCX}	 2.7 3.5	—	ns	4
MCK to MDQS	t_{DDKHMH}	–0.75	0.6	ns	5
MDQ/MECC/MDM output setup with respect to MDQS 266 MHz 200 MHz	t_{DDKHDS}, t_{DDKLDS}	 1.0 1.2	—	ns	6
MDQ/MECC/MDM output hold with respect to MDQS 266 MHz 200 MHz	t_{DDKHDX}, t_{DDKLDX}	 1.0 1.2	—	ns	6
MDQS preamble start	t_{DDKHMP}	$-0.5 \times t_{MCK} - 0.6$	$-0.5 \times t_{MCK} + 0.6$	ns	7

Table 20. DDR and DDR2 SDRAM Output AC Timing Specifications for Source Synchronous Mode (continued)

At recommended operating conditions with GV_{DD} of (1.8 V or 2.5 V) ± 5%.

Parameter[8]	Symbol[1]	Min	Max	Unit	Notes
MDQS epilogue end	t_{DDKHME}	–0.6	0.9	ns	7

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. Output hold time can be read as DDR timing (DD) from the rising or falling edge of the reference clock (KH or KL) until the output went invalid (AX or DX). For example, t_{DDKHAS} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes from the high (H) state until outputs (A) are setup (S) or output valid time. Also, t_{DDKLDX} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes low (L) until data outputs (D) are invalid (X) or data output hold time.
2. All MCK/$\overline{\text{MCK}}$ referenced measurements are made from the crossing of the two signals ±0.1 V.
3. In the source synchronous mode, MCK/$\overline{\text{MCK}}$ can be shifted in ¼ applied cycle increments through the clock control register. For the skew measurements referenced for t_{AOSKEW} it is assumed that the clock adjustment is set to align the address/command valid with the rising edge of MCK.
4. ADDR/CMD includes all DDR SDRAM output signals except MCK/$\overline{\text{MCK}}$, $\overline{\text{MCS}}$, and MDQ/MECC/MDM/MDQS. For the ADDR/CMD setup and hold specifications, it is assumed that the clock control register is set to adjust the memory clocks by ½ applied cycle.
5. Note that t_{DDKHMH} follows the symbol conventions described in note 1. For example, t_{DDKHMH} describes the DDR timing (DD) from the rising edge of the MCK(n) clock (KH) until the MDQS signal is valid (MH). t_{DDKHMH} can be modified through control of the DQSS override bits in the TIMING_CFG_2 register. In source synchronous mode, this will typically be set to the same delay as the clock adjust in the CLK_CNTL register. The timing parameters listed in the table assume that these two parameters have been set to the same adjustment value. See the *MPC8360E PowerQUICC II Pro Integrated Communications Processor Family Reference Manual* for a description and understanding of the timing modifications enabled by use of these bits.
6. Determined by maximum possible skew between a data strobe (MDQS) and any corresponding bit of data (MDQ), ECC (MECC), or data mask (MDM). The data strobe should be centered inside of the data eye at the pins of the device.
7. All outputs are referenced to the rising edge of MCK(n) at the pins of the device. Note that t_{DDKHMP} follows the symbol conventions described in note 1.
8. AC timing values are based on the DDR data rate, which is twice the DDR memory bus frequency.

Figure 6 shows the DDR SDRAM output timing for address skew with respect to any MCK.

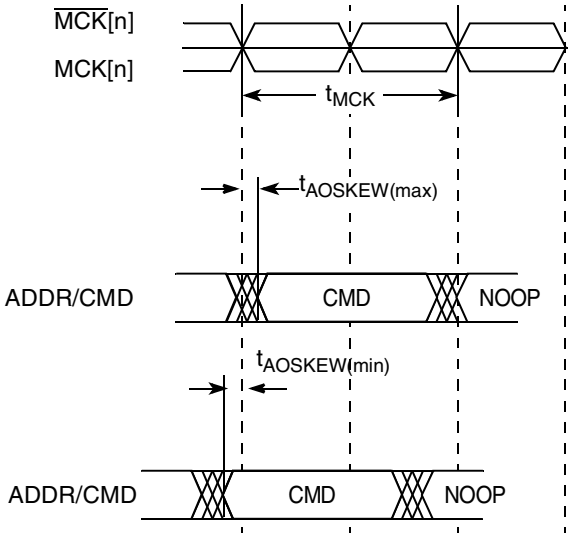

Figure 6. Timing Diagram for t_{AOSKEW} Measurement

Figure 9 shows the GMII transmit AC timing diagram.

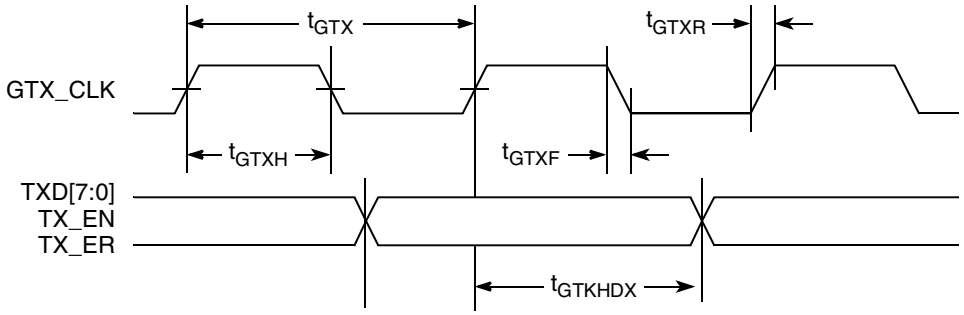

Figure 9. GMII Transmit AC Timing Diagram

8.2.1.2 GMII Receive AC Timing Specifications

Table 27 provides the GMII receive AC timing specifications.

Table 27. GMII Receive AC Timing Specifications

At recommended operating conditions with LV_{DD}/OV_{DD} of 3.3 V ± 10%.

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit	Notes
RX_CLK clock period	t_{GRX}	—	8.0	—	ns	—
RX_CLK duty cycle	t_{GRXH}/t_{GRX}	40	—	60	%	—
RXD[7:0], RX_DV, RX_ER setup time to RX_CLK	t_{GRDVKH}	2.0	—	—	ns	—
RXD[7:0], RX_DV, RX_ER hold time to RX_CLK	t_{GRDXKH}	0.3	—	—	ns	—
RX_CLK clock rise time, (20% to 80%)	t_{GRXR}	—	—	1.0	ns	—
RX_CLK clock fall time, (80% to 20%)	t_{GRXF}	—	—	1.0	ns	—

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{GRDVKH} symbolizes GMII receive timing (GR) with respect to the time data input signals (D) reaching the valid state (V) relative to the t_{RX} clock reference (K) going to the high state (H) or setup time. Also, t_{GRDXKL} symbolizes GMII receive timing (GR) with respect to the time data input signals (D) went invalid (X) relative to the t_{GRX} clock reference (K) going to the low (L) state or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{GRX} represents the GMII (G) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

Figure 32 provides the test access port timing diagram.

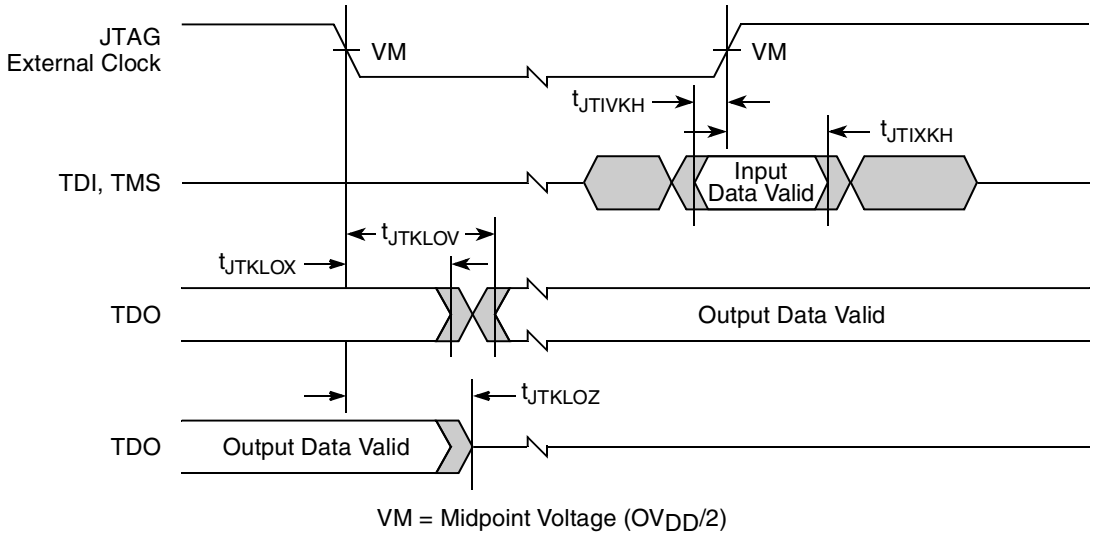

Figure 32. Test Access Port Timing Diagram

11 I²C

This section describes the DC and AC electrical characteristics for the I²C interface of the MPC8358E.

11.1 I²C DC Electrical Characteristics

Table 43 provides the DC electrical characteristics for the I²C interface of the device.

Table 43. I²C DC Electrical Characteristics

At recommended operating conditions with OV_{DD} of 3.3 V ± 10%.

Parameter	Symbol	Min	Max	Unit	Notes
Input high voltage level	V_{IH}	$0.7 \times OV_{DD}$	$OV_{DD} + 0.3$	V	—
Input low voltage level	V_{IL}	–0.3	$0.3 \times OV_{DD}$	V	—
Low level output voltage	V_{OL}	0	0.4	V	1
Output fall time from V_{IH}(min) to V_{IL}(max) with a bus capacitance from 10 to 400 pF	t_{I2KLKV}	$20 + 0.1 \times C_B$	250	ns	2
Pulse width of spikes which must be suppressed by the input filter	t_{I2KHKL}	0	50	ns	3
Capacitance for each I/O pin	C_I	—	10	pF	—
Input current ($0 V \le V_{IN} \le OV_{DD}$)	I_{IN}	—	±10	µA	4

Notes:
1. Output voltage (open drain or open collector) condition = 3 mA sink current.
2. C_B = capacitance of one bus line in pF.
3. Refer to the *MPC8360E Integrated Communications Processor Family Reference Manual* for information on the digital filter used.
4. I/O pins will obstruct the SDA and SCL lines if OV_{DD} is switched off.

11.2 I²C AC Electrical Specifications

Table 44 provides the AC timing parameters for the I²C interface of the device.

Table 44. I²C AC Electrical Specifications

All values refer to V_{IH} (min) and V_{IL} (max) levels (see Table 43).

Parameter	Symbol[1]	Min	Max	Unit
SCL clock frequency	f_{I2C}	0	400	kHz
Low period of the SCL clock	t_{I2CL}	1.3	—	µs
High period of the SCL clock	t_{I2CH}	0.6	—	µs
Setup time for a repeated START condition	t_{I2SVKH}	0.6	—	µs
Hold time (repeated) START condition (after this period, the first clock pulse is generated)	t_{I2SXKL}	0.6	—	µs
Data setup time	t_{I2DVKH}	100	—	ns

Table 47. PCI AC Timing Specifications at 33 MHz

Parameter	Symbol[1]	Min	Max	Unit	Notes
Clock to output valid	t_{PCKHOV}	—	11	ns	2
Output hold from clock	t_{PCKHOX}	2	—	ns	2
Clock to output high impedance	t_{PCKHOZ}	—	14	ns	2, 3
Input setup to clock	t_{PCIVKH}	7.0	—	ns	2, 4
Input hold from clock	t_{PCIXKH}	0.3	—	ns	2, 4

Notes:

1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{PCIVKH} symbolizes PCI timing (PC) with respect to the time the input signals (I) reach the valid state (V) relative to the PCI_SYNC_IN clock, t_{SYS}, reference (K) going to the high (H) state or setup time. Also, t_{PCRHFV} symbolizes PCI timing (PC) with respect to the time hard reset (R) went high (H) relative to the frame signal (F) going to the valid (V) state.
2. See the timing measurement conditions in the *PCI 2.2 Local Bus Specifications*.
3. For purposes of active/float timing measurements, the Hi-Z or off-state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
4. Input timings are measured at the pin.

Figure 35 provides the AC test load for PCI.

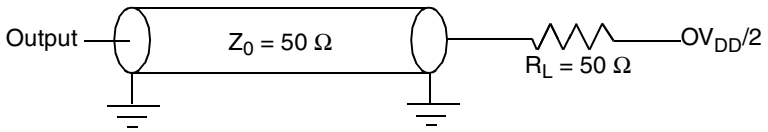

Figure 35. PCI AC Test Load

Figure 36 shows the PCI input AC timing conditions.

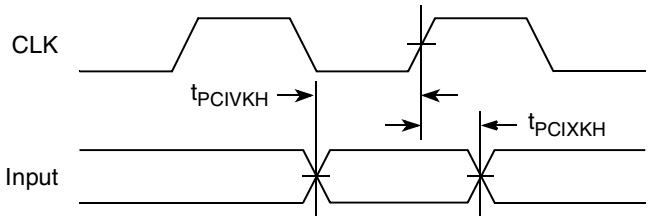

Figure 36. PCI Input AC Timing Measurement Conditions

Figure 37 shows the PCI output AC timing conditions.

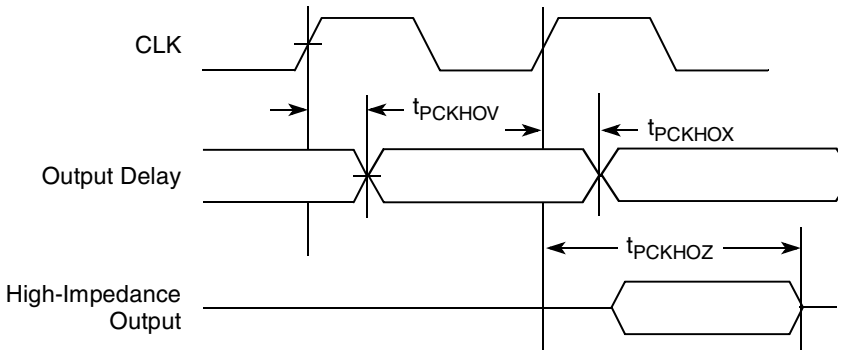

Figure 37. PCI Output AC Timing Measurement Condition

13 Timers

This section describes the DC and AC electrical specifications for the timers of the MPC8358E.

13.1 Timers DC Electrical Characteristics

Table 48 provides the DC electrical characteristics for the device timer pins, including TIN, $\overline{\text{TOUT}}$, $\overline{\text{TGATE}}$, and RTC_CLK.

Table 48. Timers DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit
Output high voltage	V_{OH}	I_{OH} = –6.0 mA	2.4	—	V
Output low voltage	V_{OL}	I_{OL} = 6.0 mA	—	0.5	V
Output low voltage	V_{OL}	I_{OL} = 3.2 mA	—	0.4	V
Input high voltage	V_{IH}	—	2.0	OV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	–0.3	0.8	V
Input current	I_{IN}	0 V ≤ V_{IN} ≤ OV_{DD}	—	±10	μA

13.2 Timers AC Timing Specifications

Table 49 provides the timer input and output AC timing specifications.

Table 49. Timers Input AC Timing Specifications[1]

Characteristic	Symbol[2]	Typ	Unit
Timers inputs—minimum pulse width	t_{TIWID}	20	ns

Notes:

1. Input specifications are measured from the 50% level of the signal to the 50% level of the rising edge of CLKIN. Timings are measured at the pin.
2. Timers inputs and outputs are asynchronous to any visible clock. Timers outputs should be synchronized before use by any external synchronous logic. Timers inputs are required to be valid for at least t_{TIWID} ns to ensure proper operation.

Figure 38 provides the AC test load for the timers.

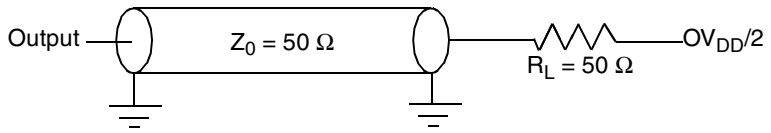

Figure 38. Timers AC Test Load

14 GPIO

This section describes the DC and AC electrical specifications for the GPIO of the MPC8358E.

14.1 GPIO DC Electrical Characteristics

Table 50 provides the DC electrical characteristics for the device GPIO.

Table 50. GPIO DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit	Notes
Output high voltage	V_{OH}	I_{OH} = –6.0 mA	2.4	—	V	1
Output low voltage	V_{OL}	I_{OL} = 6.0 mA	—	0.5	V	1
Output low voltage	V_{OL}	I_{OL} = 3.2 mA	—	0.4	V	1
Input high voltage	V_{IH}	—	2.0	OV_{DD} + 0.3	V	1
Input low voltage	V_{IL}	—	–0.3	0.8	V	—
Input current	I_{IN}	0 V ≤ V_{IN} ≤ OV_{DD}	—	±10	μA	—

Note: This specification applies when operating from 3.3-V supply.

14.2 GPIO AC Timing Specifications

Table 51 provides the GPIO input and output AC timing specifications.

Table 51. GPIO Input AC Timing Specifications[1]

Characteristic	Symbol[2]	Typ	Unit
GPIO inputs—minimum pulse width	t_{PIWID}	20	ns

Notes:
1. Input specifications are measured from the 50% level of the signal to the 50% level of the rising edge of CLKIN. Timings are measured at the pin.
2. GPIO inputs and outputs are asynchronous to any visible clock. GPIO outputs should be synchronized before use by any external synchronous logic. GPIO inputs are required to be valid for at least t_{PIWID} ns to ensure proper operation.

16.1 SPI DC Electrical Characteristics

Table 54 provides the DC electrical characteristics for the device SPI.

Table 54. SPI DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit
Output high voltage	V_{OH}	I_{OH} = –6.0 mA	2.4	—	V
Output low voltage	V_{OL}	I_{OL} = 6.0 mA	—	0.5	V
Output low voltage	V_{OL}	I_{OL} = 3.2 mA	—	0.4	V
Input high voltage	V_{IH}	—	2.0	OV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	–0.3	0.8	V
Input current	I_{IN}	0 V ≤ V_{IN} ≤ OV_{DD}	—	±10	μA

16.2 SPI AC Timing Specifications

Table 55 and provide the SPI input and output AC timing specifications.

Table 55. SPI AC Timing Specifications[1]

Characteristic	Symbol[2]	Min	Max	Unit
SPI outputs—Master mode (internal clock) delay	t_{NIKHOX} t_{NIKHOV}	0.4 —	— 8	ns
SPI outputs—Slave mode (external clock) delay	t_{NEKHOX} t_{NEKHOV}	2 —	— 8	ns
SPI inputs—Master mode (internal clock) input setup time	t_{NIIVKH}	8	—	ns
SPI inputs—Master mode (internal clock) input hold time	t_{NIIXKH}	0	—	ns
SPI inputs—Slave mode (external clock) input setup time	t_{NEIVKH}	4	—	ns
SPI inputs—Slave mode (external clock) input hold time	t_{NEIXKH}	2	—	ns

Notes:
1. Output specifications are measured from the 50% level of the rising edge of CLKIN to the 50% level of the signal. Timings are measured at the pin.
2. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{NIKHOV} symbolizes the NMSI outputs internal timing (NI) for the time t_{SPI} memory clock reference (K) goes from the high state (H) until outputs (O) are valid (V).

Figure 40 provides the AC test load for the SPI.

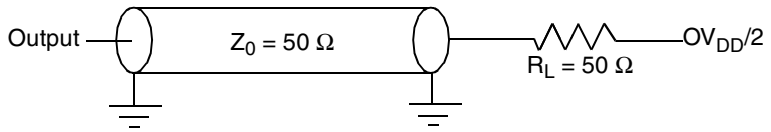

Figure 40. SPI AC Test Load

Table 59. UTOPIA AC Timing Specifications[1] (continued)

Characteristic	Symbol[2]	Min	Max	Unit	Notes
UTOPIA inputs—External clock input setup time	t_{UEIVKH}	4.2	—	ns	—
UTOPIA inputs—Internal clock input hold time	t_{UIIXKH}	2.4	—	ns	—
UTOPIA inputs—External clock input hold time	t_{UEIXKH}	1	—	ns	—

Notes:
1. Output specifications are measured from the 50% level of the rising edge of CLKIN to the 50% level of the signal. Timings are measured at the pin.
2. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{UIKHOX} symbolizes the UTOPIA outputs internal timing (UI) for the time t_{UTOPIA} memory clock reference (K) goes from the high state (H) until outputs (O) are invalid (X).

Figure 45 provides the AC test load for the UTOPIA.

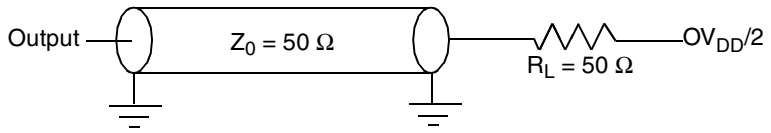

Figure 45. UTOPIA AC Test Load

Figure 46 and Figure 47 represent the AC timing from Table 55. Note that although the specifications generally reference the rising edge of the clock, these AC timing diagrams also apply when the falling edge is the active edge.

Figure 46 shows the UTOPIA timing with external clock.

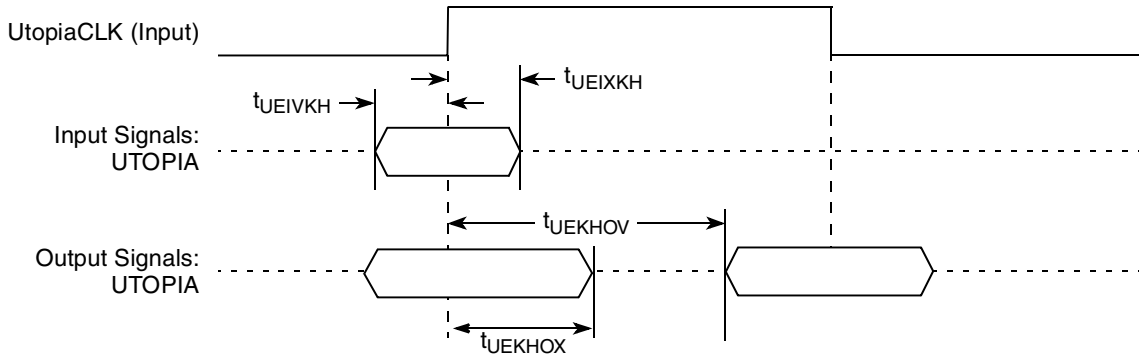

Figure 46. UTOPIA AC Timing (External Clock) Diagram

19.2 HDLC, BISYNC, Transparent, and Synchronous UART AC Timing Specifications

Table 61 and Table 62 provide the input and output AC timing specifications for HDLC, BISYNC, transparent, and synchronous UART protocols.

Table 61. HDLC, BISYNC, and Transparent AC Timing Specifications[1]

Characteristic	Symbol[2]	Min	Max	Unit
Outputs—Internal clock delay	t_{HIKHOV}	0	11.2	ns
Outputs—External clock delay	t_{HEKHOV}	1	10.8	ns
Outputs—Internal clock high impedance	t_{HIKHOX}	-0.5	5.5	ns
Outputs—External clock high impedance	t_{HEKHOX}	1	8	ns
Inputs—Internal clock input setup time	t_{HIIVKH}	8.5	—	ns
Inputs—External clock input setup time	t_{HEIVKH}	4	—	ns
Inputs—Internal clock input hold time	t_{HIIXKH}	1.4	—	ns
Inputs—External clock input hold time	t_{HEIXKH}	1	—	ns

Notes:
1. Output specifications are measured from the 50% level of the rising edge of CLKIN to the 50% level of the signal. Timings are measured at the pin.
2. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{HIKHOX} symbolizes the outputs internal timing (HI) for the time t_{serial} memory clock reference (K) goes from the high state (H) until outputs (O) are invalid (X).

Table 62. Synchronous UART AC Timing Specifications[1]

Characteristic	Symbol[2]	Min	Max	Unit
Outputs—Internal clock delay	$t_{UAIKHOV}$	0	11.3	ns
Outputs—External clock delay	$t_{UAEKHOV}$	1	14	ns
Outputs—Internal clock high impedance	$t_{UAIKHOX}$	0	11	ns
Outputs—External clock high impedance	$t_{UAEKHOX}$	1	14	ns
Inputs—Internal clock input setup time	$t_{UAIIVKH}$	6	—	ns
Inputs—External clock input setup time	$t_{UAEIVKH}$	8	—	ns
Inputs—Internal clock input hold time	$t_{UAIIXKH}$	1	—	ns
Inputs—External clock input hold time	$t_{UAEIXKH}$	1	—	ns

Notes:
1. Output specifications are measured from the 50% level of the rising edge of CLKIN to the 50% level of the signal. Timings are measured at the pin.
2. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{HIKHOX} symbolizes the outputs internal timing (HI) for the time t_{serial} memory clock reference (K) goes from the high state (H) until outputs (O) are invalid (X).

Table 65. MPC8358E PBGA Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
LGPL2/ LSDRAS/ LOE	AH19	O	OV_{DD}	—
LGPL3/ LSDCAS/ cfg_reset_source2	AE18	I/O	OV_{DD}	—
LGPL4/ LGTA/ LUPWAIT/ LPBSE	AG19	I/O	OV_{DD}	—
LGPL5/ cfg_clkin_div	AF19	I/O	OV_{DD}	—
LCKE	AD8	O	OV_{DD}	—
LCLK[0]	AC9	O	OV_{DD}	—
LCLK[1]/ LCS[6]	AG6	O	OV_{DD}	—
LCLK[2]/ LCS[7]	AE7	O	OV_{DD}	—
LSYNC_OUT	AG4	O	OV_{DD}	—
LSYNC_IN	AC8	I	OV_{DD}	—
Programmable Interrupt Controller				
MCP_OUT	AG3	O	OV_{DD}	2
IRQ0/ MCP_IN	AH4	I	OV_{DD}	—
IRQ[1:2]	AG5, AH5	I/O	OV_{DD}	—
IRQ[3]/ CORE_SRESET	AD7	I/O	OV_{DD}	—
IRQ[4:5]	AC7, AD6	I/O	OV_{DD}	—
IRQ[6:7]	AC6, AC10	I/O	OV_{DD}	—
DUART				
UART1_SOUT	AE3	O	OV_{DD}	—
UART1_SIN	AE4	I/O	OV_{DD}	—
UART1_CTS	AG2	I/O	OV_{DD}	—
UART1_RTS	AA6	O	OV_{DD}	—
I^2C Interface				
IIC1_SDA	AB6	I/O	OV_{DD}	2
IIC1_SCL	AD5	I/O	OV_{DD}	2
IIC2_SDA	AF3	I/O	OV_{DD}	2
IIC2_SCL	AH2	I/O	OV_{DD}	2
QUICC Engine				
CE_PA[0]	F6	I/O	$LV_{DD}0$	—

Table 65. MPC8358E PBGA Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
GV_{DD}	C19, C22, C25, G24, J18, J19, J20, J24, K19, K20, K26, L20, M20, M26, N19, N20, P20, P27, R20, T19, T20, T27, U19, U20, U25, V19, V20, W20, W26, Y20, AA24, AB28, AC21, AC28, AD28, AF21, AF25	Power for DDR DRAM I/O Voltage (2.5 V or 1.8 V)	GV_{DD}	—
$LV_{DD}0$	F3, J9	—	$LV_{DD}0$	—
$LV_{DD}1$	P3, P10	—	$LV_{DD}1$	10
$LV_{DD}2$	R4, R10	—	$LV_{DD}2$	10
V_{DD}	M12, M13, M16, M17, N10, N12, N13, N14, N15, N16, N17, P12, P13, P14, P15, P16, P17, R12, R13, R16, R17, T12, T13, T16, T17, U12, U13, U14, U15, U16, U17, V12, V13, V16, V17, W11, W12, W13, W15, W16, W17, Y16, Y17	Power for Core (1.2 V)	V_{DD}	—
OV_{DD}	C6, C12, D17, J11, J13, J14, K3, K9, K10, K12, K15, K16, L10, M9, N9, T9, U9, V3, V10, W9, W10, W14, Y9, Y10, Y12, Y13, Y15, AA3, AE6, AE16, AF11, AF20	PCI, 10/100 Ethernet, and other Standard (3.3 V)	OV_{DD}	—
MVREF1	J27	I	DDR Reference Voltage	—
MVREF2	Y24	I	DDR Reference Voltage	—
No Connect				
NC	F23, G23, H23, J23, K23, L23, M23, N23, P23, R23, T23, U23, V23, W23, Y23, AA23, AB23, AC23	—	—	—

Notes:
1. This pin is an open drain signal. A weak pull-up resistor (1 kΩ) should be placed on this pin to OV_{DD}.
2. This pin is an open drain signal. A weak pull-up resistor (2–10 kΩ) should be placed on this pin to OV_{DD}.
3. This output is actively driven during reset rather than being three-stated during reset.
4. These JTAG pins have weak internal pull-up P-FETs that are always enabled.
5. This pin should have a weak pull up if the chip is in PCI host mode. Follow PCI specifications recommendation.
6. These are On Die Termination pins, used to control DDR2 memories internal termination resistance.
7. This pin must always be tied to GND.
8. This pin must always be left not connected.
9. This pin must always be tied to GV_{DD}.
10. Refers to *MPC8360E PowerQUICC II™ Pro Integrated Communications Processor Reference Manual* section on “RGMII Pins” for information about the two UCC2 Ethernet interface options.
11. It is recommended that MDIC0 be tied to GND using an 18.2 Ω resistor and MDIC1 be tied to DDR power using an 18.2 Ω resistor for DDR2.

input selects whether CLKIN or CLKIN/2 is driven out on the PCI_SYNC_OUT signal. The OCCR[PCIOEN*n*] parameters enable the PCI_CLK_OUT*n*, respectively.

PCI_SYNC_OUT is connected externally to PCI_SYNC_IN to allow the internal clock subystem to synchronize to the system PCI clocks. PCI_SYNC_OUT must be connected properly to PCI_SYNC_IN, with equal delay to all PCI agent devices in the system, to allow the device to function. When the device is configured as a PCI agent device, PCI_CLK is the primary input clock. When the device is configured as a PCI agent device the CLKIN and the CFG_CLKIN_DIV signals should be tied to GND.

When the device is configured as a PCI host device (RCWH[PCIHOST] = 1) and PCI clock output is disabled (RCWH[PCICKDRV] = 0), clock distribution and balancing done externally on the board. Therefore, PCI_SYNC_IN is the primary input clock.

As shown in Figure 53, the primary clock input (frequency) is multiplied by the QUICC Engine block phase-locked loop (PLL), the system PLL, and the clock unit to create the QUICC Engine clock (*ce_clk*), the coherent system bus clock (*csb_clk*), the internal DDRC1 controller clock (*ddr1_clk*), and the internal clock for the local bus interface unit and DDR2 memory controller (*lb_clk*).

The *csb_clk* frequency is derived from a complex set of factors that can be simplified into the following equation:

$$csb\_clk = \{PCI\_SYNC\_IN \times (1 + CFG\_CLKIN\_DIV)\} \times SPMF$$

In PCI host mode, PCI_SYNC_IN × (1 + CFG_CLKIN_DIV) is the CLKIN frequency; in PCI agent mode, CFG_CLKIN_DIV must be pulled down (low), so PCI_SYNC_IN × (1 + CFG_CLKIN_DIV) is the PCI_CLK frequency.

The *csb_clk* serves as the clock input to the e300 core. A second PLL inside the e300 core multiplies up the *csb_clk* frequency to create the internal clock for the e300 core (*core_clk*). The system and core PLL multipliers are selected by the SPMF and COREPLL fields in the reset configuration word low (RCWL) which is loaded at power-on reset or by one of the hard-coded reset options. See Chapter 4, “Reset, Clocking, and Initialization,” in the *MPC8360E PowerQUICC II Pro Integrated Communications Processor Family Reference Manual* for more information on the clock subsystem.

The *ce_clk* frequency is determined by the QUICC Engine PLL multiplication factor (RCWL[CEPMF) and the QUICC Engine PLL division factor (RCWL[CEPDF]) according to the following equation:

$$ce\_clk = (\text{primary clock input} \times CEPMF) \div (1 + CEPDF)$$

The internal *ddr1_clk* frequency is determined by the following equation:

$$ddr1\_clk = csb\_clk \times (1 + RCWL[DDR1CM])$$

Note that the lb_clk clock frequency (for DDRC2) is determined by RCWL[LBCM]. The *internal ddr1_clk* frequency is not the external memory bus frequency; *ddr1_clk* passes through the DDRC1 clock divider (÷2) to create the differential DDRC1 memory bus clock outputs (MEMC1_MCK and $\overline{\text{MEMC1\_MCK}}$). However, the data rate is the same frequency as *ddr1_clk*.

The internal *lb_clk* frequency is determined by the following equation:

$$lb\_clk = csb\_clk \times (1 + RCWL[LBCM])$$

Note that *lb_clk* is not the external local bus or DDRC2 frequency; *lb_clk* passes through the a LB clock divider to create the external local bus clock outputs (LSYNC_OUT and LCLK[0:2]). The LB clock divider ratio is controlled by LCRR[CLKDIV].

In addition, some of the internal units may be required to be shut off or operate at lower frequency than the *csb_clk* frequency. Those units have a default clock ratio that can be configured by a memory mapped register after the device comes out of reset. Table 66 specifies which units have a configurable clock frequency.

Table 66. Configurable Clock Units

Unit	Default Frequency	Options
Security core	*csb_clk*/3	Off, *csb_clk*[1], *csb_clk*/2, *csb_clk*/3
PCI and DMA complex	csb_clk	Off, *csb_clk*

1 With limitation, only for slow csb_clk rates, up to 166 MHz.

Table 67 provides the operating frequencies for the PBGA package under recommended operating conditions (see Table 2). All frequency combinations shown in the table below may not be available. Maximum operating frequencies depend on the part ordered, see Section 25.1, "Part Numbers Fully Addressed by this Document," for part ordering details and contact your Freescale sales representative or authorized distributor for more information.

Table 67. Operating Frequencies for the PBGA Package

Characteristic[1]	400 MHz	Unit
e300 core frequency (*core_clk*)	266–400	MHz
Coherent system bus frequency (*csb_clk*)	133–266	MHz
QUICC Engine frequency (*ce_clk*)	266–400	MHz
DDR and DDR2 memory bus frequency (MCLK)[2]	100–133	MHz
Local bus frequency (LCLK*n*)[3]	16.67–133	MHz
PCI input frequency (CLKIN or PCI_CLK)	25–66.67	MHz
Security core maximum internal operating frequency	133	MHz

1 The CLKIN frequency, RCWL[SPMF], and RCWL[COREPLL] settings must be chosen such that the resulting *csb_clk*, MCLK, LCLK[0:2], and *core_clk* frequencies do not exceed their respective maximum or minimum operating frequencies.

2 The DDR data rate is 2x the DDR memory bus frequency.

3 The local bus frequency is 1/2, 1/4, or 1/8 of the *lb_clk* frequency (depending on LCRR[CLKDIV]) which is in turn 1x or 2x the *csb_clk* frequency (depending on RCWL[LBCM]).

- To configure the device with CSB clock rate of 266 MHz, core rate of 400 MHz, and QUICC Engine clock rate 300 MHz while the input clock rate is 33 MHz. Conf No. ‘s10’ and ‘c1’ are selected from Table 74. SPMF is 1000, CORPLL is 0000011, CEPMF is 01001, and CEPDF is 0.

23 Thermal

This section describes the thermal specifications of the MPC8358E.

23.1 Thermal Characteristics

Table 75 provides the package thermal characteristics for the 668 29 mm x 29 mm PBGA package.

Table 75. Package Thermal Characteristics for the PBGA Package

Characteristic	Symbol	Value	Unit	Notes
Junction-to-ambient Natural Convection on single layer board (1s)	$R_{\theta JA}$	20	°C/W	1, 2
Junction-to-ambient Natural Convection on four layer board (2s2p)	$R_{\theta JA}$	14	°C/W	1, 2, 3
Junction-to-ambient (@1 m/s) on single layer board (1s)	$R_{\theta JMA}$	15	°C/W	1, 3
Junction-to-ambient (@ 1 m/s) on four layer board (2s2p)	$R_{\theta JMA}$	11	•C/W	1, 3
Junction-to-board thermal	$R_{\theta JB}$	6	•C/W	4
Junction-to-case thermal	$R_{\theta JC}$	4	•C/W	5
Junction-to-Package Natural Convection on Top	Ψ_{JT}	4	•C/W	6

Notes

1. Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance.
2. Per JEDEC JESD51-2 and JEDEC JESD51-9 with the single layer board horizontal.
3. Per JEDEC JESD51-6 with the board horizontal. 1 m/sec is approximately equal to 200 linear feet per minute (LFM).
4. Thermal resistance between the die and the printed circuit board per JEDEC JESD51-8. Board temperature is measured on the top surface of the board near the package.
5. Thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1).
6. Thermal characterization parameter indicating the temperature difference between package top and the junction temperature per JEDEC JESD51-2. When Greek letters are not available, the thermal characterization parameter is written as Psi-JT.

23.2 Thermal Management Information

For the following sections, $P_D = (V_{DD} \times I_{DD}) + P_{I/O}$ where $P_{I/O}$ is the power dissipation of the I/O drivers. See Table 5 for typical power dissipations values.

23.2.3 Experimental Determination of Junction Temperature

To determine the junction temperature of the device in the application after prototypes are available, the Thermal Characterization Parameter (Ψ_{JT}) can be used to determine the junction temperature with a measurement of the temperature at the top center of the package case using the following equation:

$$T_J = T_T + (\Psi_{JT} \times P_D)$$

where:

T_J = junction temperature (°C)
T_T = thermocouple temperature on top of package (°C)
Ψ_{JT} = junction-to-ambient thermal resistance (°C/W)
P_D = power dissipation in the package (W)

The thermal characterization parameter is measured per JESD51-2 specification using a 40 gauge type T thermocouple epoxied to the top center of the package case. The thermocouple should be positioned so that the thermocouple junction rests on the package. A small amount of epoxy is placed over the thermocouple junction and over about 1 mm of wire extending from the junction. The thermocouple wire is placed flat against the package case to avoid measurement errors caused by cooling effects of the thermocouple wire.

23.2.4 Heat Sinks and Junction-to-Ambient Thermal Resistance

In some application environments, a heat sink will be required to provide the necessary thermal management of the device. When a heat sink is used, the thermal resistance is expressed as the sum of a junction to case thermal resistance and a case to ambient thermal resistance:

$$R_{\theta JA} = R_{\theta JC} + R_{\theta CA}$$

where:

$R_{\theta JA}$ = junction-to-ambient thermal resistance (°C/W)
$R_{\theta JC}$ = junction-to-case thermal resistance (°C/W)
$R_{\theta CA}$ = case-to-ambient thermal resistance (°C/W)

$R_{\theta JC}$ is device related and cannot be influenced by the user. The user controls the thermal environment to change the case-to-ambient thermal resistance, $R_{\theta CA}$. For instance, the user can change the size of the heat sink, the airflow around the device, the interface material, the mounting arrangement on printed-circuit board, or change the thermal dissipation on the printed-circuit board surrounding the device.

To illustrate the thermal performance of the devices with heat sinks, the thermal performance has been simulated with a few commercially available heat sinks. The heat sink choice is determined by the application environment (temperature, airflow, adjacent component power dissipation) and the physical space available. Because there is not a standard application environment, a standard heat sink is not required.

Millennium Electronics (MEI) Loroco Sites 671 East Brokaw Road San Jose, CA 95112 Internet: www.mei-millennium.com	408-436-8770
Tyco Electronics Chip Coolers™ P.O. Box 3668 Harrisburg, PA 17105-3668 Internet: www.chipcoolers.com	800-522-6752
Wakefield Engineering 33 Bridge St. Pelham, NH 03076 Internet: www.wakefield.com	603-635-5102

Interface material vendors include the following:

Chomerics, Inc. 77 Dragon Ct. Woburn, MA 01888-4014 Internet: www.chomerics.com	781-935-4850
Dow-Corning Corporation Dow-Corning Electronic Materials 2200 W. Salzburg Rd. Midland, MI 48686-0997 Internet: www.dowcorning.com	800-248-2481
Shin-Etsu MicroSi, Inc. 10028 S. 51st St. Phoenix, AZ 85044 Internet: www.microsi.com	888-642-7674
The Bergquist Company 18930 West 78th St. Chanhassen, MN 55317 Internet: www.bergquistcompany.com	800-347-4572

23.3 Heat Sink Attachment

When attaching heat sinks to these devices, an interface material is required. The best method is to use thermal grease and a spring clip. The spring clip should connect to the printed-circuit board, either to the board itself, to hooks soldered to the board, or to a plastic stiffener. Avoid attachment forces which would lift the edge of the package or peel the package from the board. Such peeling forces reduce the solder joint lifetime of the package. Recommended maximum force on the top of the package is 10 lb force (4.5 kg force). If an adhesive attachment is planned, the adhesive should be intended for attachment to painted or plastic surfaces and its performance verified under the application requirements.